

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

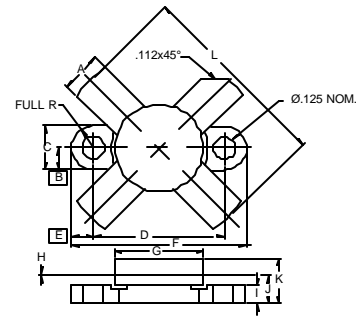
The **ASI HFT150-28** is Designed for

FEATURES:

- $P_G = 16$ dB min. at 150 W/30 MHz
- $IMD_3 = -28$ dBc max. at 150 W_(PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_D	16 A
$V_{(BR)DSS}$	65 V
V_{GS}	± 40 V
P_{DISS}	300 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
q_{JC}	$0.60^\circ C/W$

PACKAGE STYLE .500 4L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.125 / 3.18	
C	.245 / 6.22	.255 / 6.48
D	.720 / 18.28	.730 / 18.54
E	.125 / 3.18	
F	.970 / 24.64	.980 / 24.89
G	.495 / 12.57	.505 / 12.83
H	.003 / 0.08	.007 / 0.18
I	.090 / 2.29	.110 / 2.79
J	.150 / 3.81	.175 / 4.45
K	.280 / 7.11	
L	.980 / 24.89	1.050 / 26.67

ORDER CODE: ASI10616
CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)DSS}$	$V_{GS} = 0$ V $I_{DS} = 100$ mA	65	---	---	V
I_{DSS}	$V_{GS} = 0$ V $V_{DS} = 28$ V	---	---	0.5	mA
I_{GSS}	$V_{GS} = 20$ V $V_{DS} = 0$ V	---	---	1.0	mA
V_{GS}	$V_{DS} = 10$ V $I_D = 100$ mA	1.0	---	5.0	V
V_{DS}	$V_{GS} = 10$ V $I_D = 10$ A	---	---	1.5	V
G_{FS}	$V_{DS} = 10$ V $I_D = 5$ A	3.5	---	---	mho
C_{ISS} C_{OSS} C_{RSS}	$V_{GS} = 28$ V $V_{DS} = 0$ V $F = 1.0$ MHz	---	375 188 26	---	pF
P_{IN} G_{PS} h	$V_{DD} = 28$ V $I_{DQ} = 250$ mA $P_{OUT} = 150$ W (PEP) $f = 175$ MHz	50	10	15	W dB %